AC7023E2 Datasheet

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AC7023E2 Features

CPU

- 32-bit DSP
- with IEEE754 Single precision FPU
- Up to 160MHz programmable processor
- 64Vectored interrupts
- 8 Levels interrupt priority

Clocks

24 MHz crystal oscillator

DSP Audio Processing

- SBC, AAC Audio decodes supported for BT audio
- mSBC voice codec supported for BT phone
- Packet Loss Concealment (PLC) for voice processing
- Single MIC Environmental Noise Cancellation (ENC)
- Single-band DRC limiter
- Multi-band EQ configuration for voice Effects

Audio Codec

- Two channels 24-bit DAC,SNR ≥ 99dB
- One channels 16-bit ADC,SNR ≥ 85dB
- Audio DAC Sampling rates of 8kHz/11.025kHz/16kHz/22.05kHz/24kHz/32kHz/44.1kHz/48kHz are supported
- Audio ADC Sampling rates of 8kHz/11.025kHz/16kHz/22.05kHz/24kHz/32 kHz/44.1kHz/48kHz are supported
- One channels analog audio inputs
- Audio DAC supports differential cap-less mode or single-ended mode or vcmo-stero mode
- Direct drive 16ohm/32ohm Speaker loading

Bluetooth

- Compliant with BluetoothV5.3+BR+EDR+BLE specification
- Meet class2 and class3 transmitting power

requirement

- Maximum +8dbm transmitting power
- EDR receiver with minimum -94dBm sensitivity
- Support a2dp\avctp\avdtp\avrcp\hfp\spp\smp\ att\gap\gatt\rfcomm\sdp\l2cap profile
- a2dp 1.3.2\avctp 1.4\avdtp 1.3\ avrcp 1.6.2\hfp 1.8 \spp 1.2\rfcomm 1.1\pnp 1.3\hid 1.1.1\sdp core5.3\12cap core 5.3

Peripherals

- full speed USB OTG controller
- multi-function 32-bit timers, support capture and PWM mode
- Uart interface support DMA
- I2C Master/Slave interface
- Low power CapSense
- 10-bit ADC for analog sampling
- Individually programmable and multiplexed GPIO pins
- external interrupt/wake-up source(low power available,can be multiplexed to any I/O)

PMU

- Built-in lithium battery charging manager,up to 200mA charging current
- Built-in LDO and Buck DC-DC converter
- Soft-off mode current
 Build-in LP_Touch off:
 ≤3uA(AC702N_FLASH_SDK_vx.x.x)
 ≤7uA(AC702N_release_vx.x.x)
 Build-in LP Touch on: ≤13uA
- VPWR range : 4.5V to 5.5V
- VBAT range : 2.7V to 4.5V
- IOVDD range : 2.0V to 3.4V

Packages

QFN20(3mm*3mm)



Temperature

• Operating temperature: -40°C to +85°C

Storage temperature: -65°C to +150°C

Applications

Bluetooth Stereo Headset and Headphone

Bluetooth Lightning Earphone





1 Block Diagram

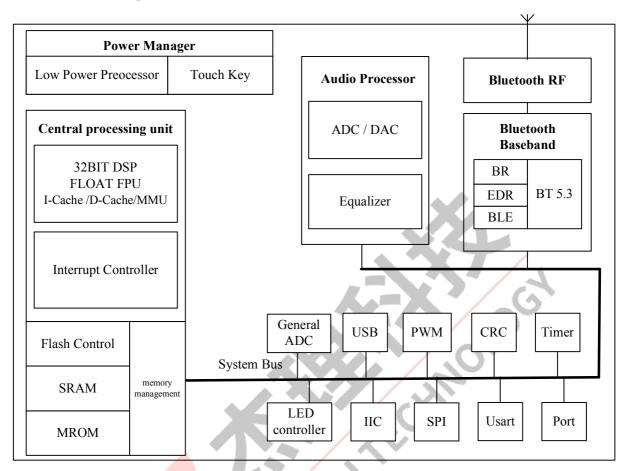


Figure 1-1 AC7023E Block Diagram



2 Pin Definition

2.1 Pin Assignment

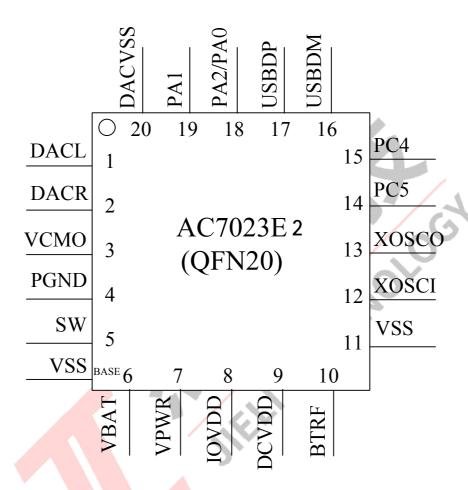


Figure 2-1 AC7023E Package Diagram



2.2 Pin Description

Table 2-1 AC7023E Pin Description

Pin No.	Pin name	Туре	Function	Other function		
1	DACL	AO	Analog Output	Left channel audio output positive;		
2	DACR	AO	Analog Output	Right channel audio output positive;		
3	VCMO	P		-		
4	PGND	G		The ground of Buck DC-DC converter;		
5	SW	РО		Switch signal of the Buck converter, connected to inductor;		
6	VBAT	PI	GPIO	Battery interface;		
7	VPWR (PP0)	PI (I/O)	GPIO (High Voltage Input)	Charge Power Input; UART0TXC: Uart0 Data Output(C); UART0RXC: Uart0 Data Input(C); PWM3: Timer3 PWM Output; CAP1: Timer1 Capture;		
8	IOVDD	PO		IO Power;		
9	DCVDD	P		DCDC power 1.25V;		
10	BTRF	RFI		Bluetooth RF antenna interface;		
11	VSS	G		Ground;		
12	XOSCI	I		System Crystal Oscillator Input;		
13	XOSCO	0		System Crystal Oscillator Output;		
14	PC5	I/O	GPIO	IIC_SDA_B : IIC Data(B); ADC5 :ADC Input Channel 5; UART2RXD :Uart2 Data In(D);		
15	PC4	I/O	GPIO	IIC_SCL_B: IIC Serial Clock(B); ADC4: ADC Input Channel 4; UART2TXD: Uart2 Data Out(D); PWM4: Timer4 PWM Output;		
16	USBDM	I/O	USB Negative Data (pull down)	IIC_SDA_A: IIC SDA(A); ADC11: ADC Input Channel 11; UART1RXD: UART1 Data In(D);		
17	USBDP	I/O	USB Positive Data (pull down)	IIC_SCL_A: IIC Clock(A); ADC10 :ADC Input Channel 10; UART1TXD :Uart1 Data Out(D);		



	PA2	I/O	GPIO	CLKOUT1: Clock Out1; MICBIAS0: MICO Bias Output(Built-in resistor); UART1RXC: Uart1 Data In(C); CAP3: Timer3 Capture;
18	PA0	I/O	GPIO	MICLDO: MIC0 Input Channel 0; UART2RXA: Uart2 Data In(A); CAP2: Timer2 Capture;
19	PA1	I/O	GPIO	MICIN0 :MIC0 Input Channel 0; UART1TXC :Uart1 Data Out(C); PWM0 :Timer0 PWM Output;
20	DACVSS	G		Ground;
BASE	VSS	G		Ground;

Pin Type	Description	Pin Type	Description
P	Power	I/O	Input or Output
PO	Power Output	I /	Input
PI	Power Input	0	Output
G	Ground	RFI	Radio frequency interface
AO	Analog Output		



3 Electrical Characteristics

3.1 Absolute Maximum Ratings

Table 3-1

Symbol	Parameter	Min	Max	Unit
Topt	Operating temperature	-40	+85	°C
Tstg	Storage temperature	-65	+150	°C
VBAT	Supply Voltage	-0.3	4.5	V
VPWR	Charger Voltage	-0.3	6	V
V _{IOVDD}	Voltage applied at IOVDD	-0.3	3.6	V
V _{GPIO}	Voltage applied to GPIO	-0.3	IOVDD+0.3	V
V _{HVIO}	Voltage applied to High Voltage Resistant IO	-0.3	+5.5	V

Note: The chip can be damaged by any stress in excess of the absolute maximum ratings listed below

3.2 PMU Characteristics

Table 3-2

Symbol	Parameter	Min	Тур	Max	Unit	Test Conditions
VBAT	Voltage Input	2.2	3.7	4.5	V	
VPWR	Charger supply Voltage	4.5	5.0	5.5	V	
Operating mod	e	****		/ .\		
IOVDD	Voltage output	-	3.0		V	VBAT = 4.2V, 10mA loading
IOVDD	Loading current	-		200	mA	IOVDD=3.2V@VBAT=3.5V
	Voltage output	_	1.25		V	IOVDD=3.0V, 10mA loading
DCVDD	Loading current	-		60	mA	DCVDD=1.25V@IOVDD=3.0v on LDO mode
		-	-	150	mA	DCVDD=1.25V@VBAT=3.0v on DCDC mode
Low Power mo	ode					
IOVDD	Loading current	_	_	10	mA	IOVDD=3V@VBAT = 4.2V



3.3 Battery Charge

Table 3-3

Symbol	Parameter	Min	Тур	Max	Unit	Test Conditions
VPWR	Charge Input Voltage	4.5	5	5.5	V	-
V _{bat float}	Charge Voltage	4.15	4.2	4.25	V	VPWR>4.5V
I _{bat}	Charge Current	20	_	200	mA	Charge current at fast charge mode VBAT=4.0V@VPWR=5.0V
$ m I_{end}$	End Of Charge Current	2	_	30	mA	End of charge current
V_{Trikl}	Trickle Charge Voltage	_	3.0	-	V	VPWR>4.5V

3.4 IO Input/Output Electrical Logical Characteristics

Table 3-4

GPIO input	GPIO input characteristics									
Symbol	Parameter	Min	Тур	Max	Unit	Test Conditions				
V_{IL}	Low-Level Input Voltage	-0.3	- /	0.3* IOVDD	V	IOVDD = 3.0V				
$ m V_{IH}$	High-Level Input Voltage	0.7* IOVDD		IOVDD+0.3	V	IOVDD = 3.0V				
High Voltage	Resistant IO input char	racteristics								
Symbol	Parameter	Min	Тур	Max	Unit	Test Conditions				
V _{IL}	Low-Level Input Voltage	-0.3) <u>-</u>	0.3* IOVDD	V	IOVDD = 3.0V				
$ m V_{IH}$	High-Level Input Voltage	0.7* IOVDD	_	+5V	V	IOVDD = 3.0V				
GPIO & Hig	h Voltage Resist <mark>ant IO</mark> o	output characteris	tics							
Symbol	Parameter	Min	Тур	Max	Unit	Test Conditions				
$ m V_{OL}$	Low-Lev <mark>el Output</mark> Voltage	_	_	0.1* IOVDD	V	IOVDD = 3.0V				
$V_{ m OH}$	High-Level Output Voltage	0.9* IOVDD	_	_	V	IOVDD = 3.0V				



3.5 Internal Resistor Characteristics

Table 3-5

Port	Drive(mA)		Internal Pull-Up Resistor	Internal Pull-Down Resistor	Comment
	HD,HD0==0,0	2.4			
PA1,PA2	HD,HD0==0,1	8	10K	10K	
PC4,PC5	HD,HD0==1,0	26	101	10K	1. PB1 default pull up
	HD,HD0==1,1 46				2、USBDM & USBDP default
PP0(VPWR)	8 (High Voltage Resis	8 (High Voltage Resistant)		10K	pull Down
PA0	8	8		10K	3. internal pull-up / pull-down
USBDP	4		1.5K	15K	resistance accuracy ±20%
USBDM	4		180K	15K	

3.6 Audio DAC Characteristics

Audio Format: SBC

Table 3-6

Parameter	Min	Тур	Max	Unit	Test Conditions
Frequency Response	20		20k	Hz	1KHz/0dB
Output Swing	2.5	0.35	0.68	Vrms	32 ohm loading
THD+N		-68		dB	With A-Weighted Filter
S/N		95	98	dB	VCMO-Stero Mode
			\rangle \text{'}		1KHz/-60dB
Dymomic Rongo		96	98	dB	32 ohm loading
Dynamic Range	-	90	98	ub	With A-Weighted Filter
					VCMO-Stero Mode
Noise Floor		6		uVrms	A-Weighted Filter
DAC Output Boycer		7.8	14	mW	32ohm loading
DAC Output Power		7.8	14	III W	VCMO-Stero Mode

3.7 Audio ADC Characteristics

Audio Filter: A-Weighted

Table 3-7

Parameter	Min	Тур	Max	Unit	Test Conditions	
D		0.5		dB	Fsample=44.1kHz,Gain=6dB	
Dynamic Range	_	85	_		Fin=1KHz 320mVrms	
SNR	_	85	_	dB	Fsample=44.1kHz,Gain=6dB	
THD+N	_	-70	_	dB	Fin=1KHz 320mVrms	
SNR	_	77	_	dB	Fsample=44.1kHz,Gain=16dB	
THD+N	_	-65	_	dB	Fin=1KHz 90mVrms	



3.8 BT Characteristics

3.8.1 Transmitter

Basic Data Rate

Table 3-8

Paramete	r	Min	Тур	Max	Unit	Test Conditions		
RF Transmit Power, DH5			6	8	dBm			
RF Power Control R	ange, DH1		20		dB	25℃,		
20dB Bandwidth	DH5		920		KHz	Power Supply		
Adjacent Channel	+2MHz		-53		dBm	VBAT>=3.7V		
Transmit Power, DH1	-2MHz		-50		dBm	2441MHz		
(BQB Test Mode RF Tx Power=3.6dBm)	+3MHz		-55		dBm	4 Layer Board		
RI_IXTOWEL 5.0dBill)	-3MHz		-53		dBm			
Enhanced Data Rate Table 3-9								

Paramete	Min	Тур	Max	Unit	Test Conditions	
Relative Pov		-1.4		dB		
	DEVM RMS		6		%	25℃
π/4 DQPSK Modulation Accuracy	DEVM 99%		11		%	Power Supply
Wiodulation Accuracy	DEVM Peak	1	16	()	%	VBAT >=3.7V
In-band spurious	+2MHz		-42		dBm	2441MHz
Emissions	-2MHz		-38		dBm	2DH5
(BQB Test Mode	+3MHz		-46		dBm	4 Layer Board
RF_Tx Power=3.6dBm)	-3MHz		-40		dBm	

3.8.2 Receiver

Basic Data Rate

Table 3-10

Parameter		Min	Тур	Max	Unit	Test Conditions
Sensitivity			-91		dBm	
Co-channel Interference Rejection			4		dB	25℃,
	+1MHz		-26		dB	Power Supply
	-1MHz		-25		dB	VBAT>=3.7V
Adjacent Channel	+2MHz		-40		dB	2441MHz
Interference Rejection	-2MHz		-35		dB	DH1
	+3MHz		-42		dB	4 Layer Board
	-3MHz		-36		dB	



Enhanced Data Rate Table 3-11

Parameter		Min	Тур	Max	Unit	Test Conditions
Sensitivity		-94	-92		dBm	
Co-channel Interference Rejection			10		dB	[25℃,
	+1MHz		-27		dB	Power Supply
	-1MHz		-26		dB	VBAT>=3.7V
Adjacent Channel	+2MHz		-31		dB	2441MHz
Interference Rejection	-2MHz		-28		dB	2DH5
	+3MHz		-37		dB	4 Layer Board
	-3MHz		-24		dB	-

3.9 ESD Protection

Table 3-12

Parameter	Тур.	Test pin	Reference standard
Human Body Mode	±4KV	All pins	JEDEC EIA/JESD22-A114
Machine Mode	±200V	All pins	JEDEC EIA/JESD22-A115
Charge Device Model	±1KV	All pins	JEDEC EIA/JESD22-C101F
Latela	±200mA	All GPIO pins	IEDEC CTANDADO NO 70E
Latch up	1.5xVopmax	All power pins	JEDEC STANDARD NO.78E

Note: 1.5xVopmax = 1.5 times maximum operating voltage.



4 Package Information

4.1 QFN20_3.0x3.0

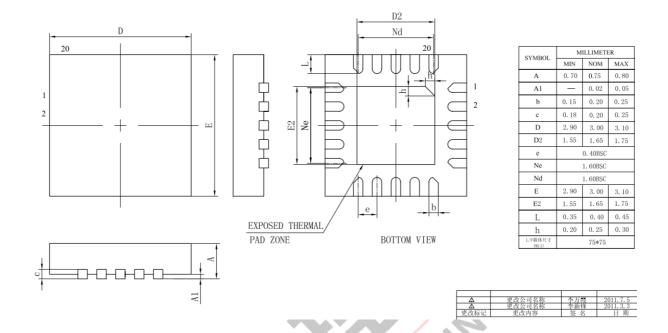


Figure 4-1 AC7023E Package



5 Solder-Reflow Condition

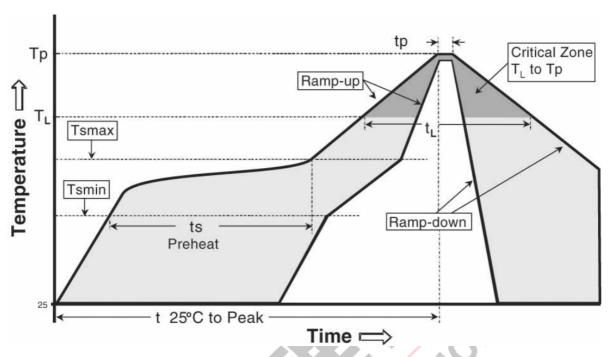


Figure 5-1 Classification Reflow Profile

Classification Profiles

Table 5-1

	Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly	
Temperature Min (T _{smin})		100℃	150℃	
Preheat/	Temperature Max (T _{smax})	150℃	200℃	
Soak	Time (ts) from (T _{smin} to T _{smax})	60-120 seconds	60-180 seconds	
Average ra	amp-up rate $(T_{smax} \text{ to } T_p)$	3 ℃/second max	3°C/second max	
Liquidous temperature (T _L)		183℃	217℃	
Time (t _L) maintained above T _L		60-150 seconds	60-150 seconds	
Peak package body temperature (T _p)		See Table 5-2	See Table 5-3	
Time within 5°C of actual Peak Temperature (tp) ²		10.20 gagands		
Ramp-down rate $(T_p \text{ to } T_L)$		6°C/second max	6°C/second max	
Time 25℃ to peak temperature		6 minutes max	8 minutes max	

Note 1: All temperatures refer to topside of the package, measured on the package body surface.

Note 2: Time within 5°C of actual peak temperature (tp) specified for the reflow profiles is a "supplier" minimum and "user" maximum.



<u>SnPb - Classification Temperature</u> Table 5-2					
Package	Volume mm ³	Volume mm ³			
Thickness	< 350	≥ 350			
<2.5 mm	240 +0/-5°C	225 +0/-5℃			
≥2.5 mm	225 +0/-5°C	225 +0/-5℃			

Pb-free - Classification Temperature

_			_	_
10	h	\mathbf{a}	-	
19	nı	16	. 7.	'

Package	Volume mm ³	Volume mm ³	Volume mm ³
Thickness	< 350	350 - 2000	> 2000
< 1.6mm	260℃	260℃	260℃
1.6 mm - 2.5mm	260℃	250℃	245℃
> 2.5mm	250℃	245°C	245°C

^{*}Tolerance:The device manufancturer/supplier shall assure process compatibility up to and including the stated classification temperature (this means Peak reflow temperature +0°C.For example 260°C+0°C)at the rated MSL level.

6 Revision History

Date	Revision	Description
2022.09.06	V1.0	Initial Release
2022.12.20	V1.1	Update resource description